

Searching PAJ

DEC 10 2010 ページ

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 52-004789

(43)Date of publication of application : 14.01.1977

---

(51)Int.Cl.

H01L 29/78  
H01L 29/40  
H01L 21/28

---

(21)Application number : 50-081177

(71)Applicant : FUJITSU LTD

(22)Date of filing : 30.06.1975

(72)Inventor : INAYOSHI KATSUYUKI  
MAEDA KAZUO

---

(54) SEMICONDUCTOR EQUIPMENT

(57)Abstract:

PURPOSE: To revent contamination of gate insulation film by forming poly-crystal Si-film under Al electrode and thus improving MIS-FET.